

PRELIMINARY

June 1994

Dual, High Speed, Low Power, Video Closed Loop Buffer

Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- User Programmable For Closed-Loop Gains of +1, -1 or +2 Without Use of External Resistors
- Standard Operational Amplifier Pinout
- Low Supply Current. 5.9mA/Op Amp (Typ)
- Excellent Gain Accuracy. 0.99V/V (Typ)
- Wide -3dB Bandwidth 340MHz (Typ)
- Fast Slew Rate 1155V/ μ s (Typ)
- High Input Impedance 1M Ω (Typ)
- Excellent Gain Flatness (to 50MHz) ± 0.02 dB (Typ)
- Fast Overdrive Recovery. <10ns (Typ)

Applications

- Flash A/D Driver
- Video Switching and Routing
- Pulse and Video Amplifiers
- Wideband Amplifiers
- RF/IF Signal Processing
- Medical Imaging Systems

Description

The HFA1212/883 is a dual closed loop Buffer featuring user programmable gain and high speed performance. Manufactured on Intersil's proprietary complementary bipolar UHF-1 process, this device offers wide -3dB bandwidth of 340MHz, very fast slew rate, excellent gain flatness and high output current.

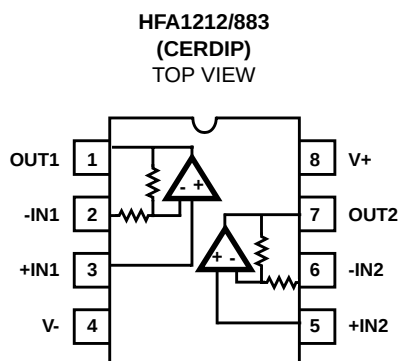
A unique feature of the pinout allows the user to select a voltage gain of +1, -1, or +2, without the use of any external components. Gain selection is accomplished via connections to the inputs, as described in the "Application Information" section. The result is a more flexible product, fewer part types in inventory, and more efficient use of board space.

Compatibility with existing op amp pinouts provides flexibility to upgrade low gain amplifiers, while decreasing component count. Unlike most buffers, the standard pinout provides an upgrade path should a higher closed loop gain be needed at a future date.

Ordering Information

PART NUMBER	TEMPERATURE RANGE	PACKAGE
HFA1212MJ/883	-55°C to +125°C	8 Lead CerDIP

Pinout



Specifications HFA1212/883

Absolute Maximum Ratings

Voltage Between V+ and V- 12V
 Voltage at Either Input Terminal V+ to V-
 Output Current (Note 1) Short Circuit Protected
 Output Current (50% Duty Cycle, Note 1) 60mA
 Junction Temperature +175°C
 ESD Rating > 2000V
 Storage Temperature Range -65°C ≤ T_A ≤ +150°C
 Lead Temperature (Soldering 10s) +300°C

Thermal Information

Thermal Resistance θ_{JA} θ_{JC}
 CerDIP Package 115°C/W 30°C/W
 Maximum Package Power Dissipation at +75°C
 CerDIP Package 0.87W
 Package Power Dissipation Derating Factor above +75°C
 CerDIP Package 8.7mW/°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

Operating V_{SUPPLY} (±V_S) ±5V R_L ≥ 50Ω
 Operating Temperature Range -55°C ≤ T_A ≤ +125°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: V_{SUPPLY} = ±5V, A_V = +1, R_{SOURCE} = 0Ω, R_L = 100Ω, V_{OUT} = 0V, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Output Offset Voltage	V _{OS}	V _{CM} = 0V	1	+25°C	-10	10	mV
			2, 3	+125°C, -55°C	-20	20	mV
Channel-to-Channel Output Offset Voltage Mismatch	ΔV _{OS}	V _{CM} = 0V	1	+25°C	-15	15	mV
			2, 3	+125°C, -55°C	-30	30	mV
Common Mode Rejection Ratio	CMRR	ΔV _{CM} = ±1.8V V+ = 3.2V, V- = -6.8V V+ = 6.8V, V- = -3.2V	1	+25°C	42	-	dB
			2	+125°C	39	-	dB
		ΔV _{CM} = ±1.2V V+ = 3.8V, V- = -6.2V V+ = 6.2V, V- = -3.8V	3	-55°C	39	-	dB
Power Supply Rejection Ratio	PSRRP	ΔV _{SUPPLY} = ±1.8V V+ = 6.8V, V- = -5V V+ = 3.2V, V- = -5V	1	+25°C	45	-	dB
			2	+125°C	42	-	dB
		ΔV _{SUPPLY} = ±1.2V V+ = 6.2V, V- = -5V V+ = 3.8V, V- = -5V	3	-55°C	42	-	dB
	PSRRN	ΔV _{SUPPLY} = ±1.8V V+ = 5V, V- = -6.8V V+ = 5V, V- = -3.2V	1	+25°C	45	-	dB
			2	+125°C	42	-	dB
		ΔV _{SUPPLY} = ±1.2V V+ = 5V, V- = -6.2V V+ = 5V, V- = -3.8V	3	-55°C	42	-	dB
Non-Inverting Input (+IN) Current	I _{BSP}	V _{CM} = 0V	1	+25°C	-15	15	μA
			2, 3	+125°C, -55°C	-25	25	μA
Channel-to-Channel +IN Current Mismatch	ΔI _{BSP}	V _{CM} = 0V	1	+25°C	-15	15	μA
			2, 3	+125°C, -55°C	-25	25	μA

Specifications HFA1212/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_{SOURCE} = 0\Omega$, $R_L = 100\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
+IN Current Common Mode Sensitivity	CMS_{IBP}	$\Delta V_{CM} = \pm 1.8V$ $V_+ = 3.2V$, $V_- = -6.8V$ $V_+ = 6.8V$, $V_- = -3.2V$	1	+25°C	-	1.25	$\mu A/V$
			2	+125°C	-	2.85	$\mu A/V$
		$\Delta V_{CM} = \pm 1.2V$ $V_+ = 3.8V$, $V_- = -6.2V$ $V_+ = 6.2V$, $V_- = -3.8V$	3	-55°C	-	2.85	$\mu A/V$
+IN Resistance	$+R_{IN}$	Note 2	1	+25°C	800	-	k Ω
			2, 3	+125°C, -55°C	350	-	k Ω
Gain	A_{VP1}	$A_V = +1$ $V_{IN} = -1V$ to +1V	1	+25°C	0.98	1.02	V/V
			2, 3	+125°C, -55°C	0.975	1.025	V/V
	A_{VM1}	$A_V = -1$ $V_{IN} = -1V$ to +1V	1	+25°C	-0.98	-1.02	V/V
			2, 3	+125°C, -55°C	-0.975	-1.025	V/V
	A_{VP2}	$A_V = +2$ $V_{IN} = -1V$ to +1V	1	+25°C	1.96	2.04	V/V
			2, 3	+125°C, -55°C	1.95	2.05	V/V
Channel-to-Channel Gain Mismatch	ΔA_{VP1}	$A_V = +1$ $V_{IN} = -1V$ to +1V	1	+25°C	-0.02	0.02	V/V
			2, 3	+125°C, -55°C	-0.025	0.025	V/V
	ΔA_{VM1}	$A_V = -1$ $V_{IN} = -1V$ to +1V	1	+25°C	-0.025	0.025	V/V
			2, 3	+125°C, -55°C	-0.025	0.025	V/V
	ΔA_{VP2}	$A_V = +2$ $V_{IN} = -1V$ to +1V	1	+25°C	-0.04	0.04	V/V
			2, 3	+125°C, -55°C	-0.05	0.05	V/V
Output Voltage Swing	V_{OP100}	$A_V = -1$ $R_L = 100\Omega$ $V_{IN} = -3.2V$ $V_{IN} = -3V$	1	+25°C	3	-	V
			2, 3	+125°C, -55°C	2.8	-	V
	V_{ON100}	$A_V = -1$ $R_L = 100\Omega$ $V_{IN} = +3.2V$ $V_{IN} = +3V$	1	+25°C	-	-3	V
			2, 3	+125°C, -55°C	-	-2.8	V
Output Voltage Swing	V_{OP50}	$A_V = -1$ $R_L = 50\Omega$ $V_{IN} = -2.7V$ $V_{IN} = -2.25V$ $V_{IN} = -2.25V$	1	+25°C	2.5	-	V
			2	+125°C	2.0	-	V
			3	-55°C	1.4	-	V
	V_{ON50}	$A_V = -1$ $R_L = 50\Omega$ $V_{IN} = +2.7V$ $V_{IN} = +2.25$ V $V_{IN} = +2.25$ V	1	+25°C	-	-2.5	V
			2	+125°C	-	-2.0	V
			3	-55°C	-	-1.4	V

Specifications HFA1212/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_{SOURCE} = 0\Omega$, $R_L = 100\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Output Current	$+I_{OUT}$	Note 3	1	+25°C	50	-	mA
			2	+125°C	40	-	mA
			3	-55°C	28	-	mA
	$-I_{OUT}$	Note 3	1	+25°C	-	-50	mA
			2	+125°C	-	-40	mA
			3	-55°C	-	-28	mA
Quiescent Power Supply Current	I_{CC}	$R_L = 100\Omega$	1	+25°C	5.6	6.1	mA/Op Amp
			2, 3	+125°C, -55°C	5.2	6.5	mA/Op Amp
	I_{EE}	$R_L = 100\Omega$	1	+25°C	-6.1	-5.6	mA/Op Amp
			2, 3	+125°C, -55°C	-6.5	-5.2	mA/Op Amp

NOTES:

- Output is short circuit protected to ground. Brief short circuits to ground will not degrade reliability, however continuous (100% duty cycle) output current must not exceed 30mA for maximum reliability.
- Guaranteed from +IN Common Mode Rejection Test, by: $+R_{IN} = 1/CMS_{IBP}$.
- Guaranteed from V_{OUT} Test with $R_L = 50\Omega$, by: $I_{OUT} = V_{OUT}/50\Omega$.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

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TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

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TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLE 1)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1(Note 1), 2, 3
Group A Test Requirements	1, 2, 3
Groups C and D Endpoints	1

NOTE:

- PDA applies to Subgroup 1 only.

Die Characteristics

DIE DIMENSIONS:

69 x 92 x 19 mils $\pm$ 1 mils

1750 x 2330 x 483 μ m $\pm$ 25.4 μ m

METALLIZATION:

Type: Metal 1: AlCu(2%)/TiW

Thickness: Metal 1: 8k $\text{\AA}$ $\pm$ 0.4k $\text{\AA}$

Type: Metal 2: AlCu(2%)

Thickness: Metal 2: 16k $\text{\AA}$ $\pm$ 0.8k $\text{\AA}$

GLASSIVATION:

Type: Nitride

Thickness: 4k $\text{\AA}$ $\pm$ 0.5k $\text{\AA}$

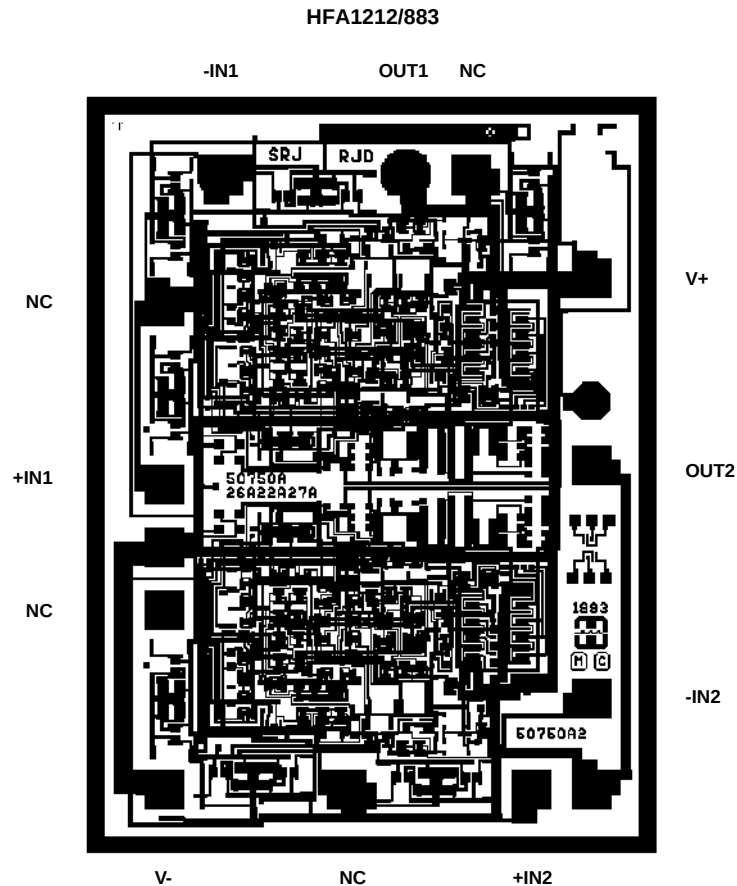
WORST CASE CURRENT DENSITY:

TBD

TRANSISTOR COUNT: 150

SUBSTRATE POTENTIAL (Powered Up): Floating (Recommend Connection to V-)

Metallization Mask Layout



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